



TSMC-02-066

September 12, 2003

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/600,393 06/20/03

Chi-Chun Chen et al.

METHOD OF FORMING DUAL GATE
INSULATOR LAYERS FOR CMOS
APPLICATIONS

Grp. Art Unit: _____

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56. Copies of each document is included herewith.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on September 19, 2003.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 9/19/03

U.S. Patent 6,110,842 to Okuno et al., "Method of Forming Multiple Gate Oxide Thicknesses Using High Density Plasma Nitridation," discloses a process for multiple gate oxides thicknesses using plasma nitridation.

U.S. Patent 6,030,862 to Kepler, "Dual Gate Oxide Formation with Minimal Channel Dopant Diffusion," discloses a DGO process.

U.S. Patent 5,960,289 to Tsui et al., "Method for Making a Dual-Thickness Gate Oxide Layer Using a Nitride/Oxide Composite Region," reveals a DGO using a N/O composition.

U.S. Patent 6,262,455 to Lutze et al., "Method of Forming Dual Gate Oxide Layers of Varying Thickness on a Single Substrate," discloses a DGO process.

U.S. Patent 6,037,224 to Buller et al., "Method for Growing Dual Oxide Thickness Using Nitrided Oxides for Oxidation Suppression," discloses a DGO using nitrided oxides.

Sincerely,

A handwritten signature in black ink, appearing to be 'SBA', written over the printed name.

Stephen B. Ackerman,
Reg. No. 37761

Form PTO-1449

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION
(Use several sheets if necessary)

DOIP
SEP 22 2003
U.S. PATENT & TRADEMARK OFFICE

Doc No. (Specimen)

TSMC-02-066

Application Number

10/600,393

Applicant

Chi-Chun Chen et al.

Filing Date

06/20/03

Group Art Unit

PATENT DOCUMENTS									
EXAMINER INITIAL	DOCUMENT NUMBER							DATE	NAME
	6	1	1	0	8	4	2	8/29/00	Okuno et al.
	6	0	3	0	8	6	2	2/29/00	Kepler
	5	9	6	0	2	8	9	9/28/99	Tsui et al.
	6	2	6	2	4	5	5	7/17/01	Lutze et al.
	6	0	3	7	2	2	4	3/14/00	Buller et al.

FOREIGN PATENT DOCUMENTS									
	DOCUMENT NUMBER							DATE	COUNTRY

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)									

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant